ESD Protection Diode

Micro-Packaged Diodes for ESD Protection

ESD7551, SZESD7551

The ESD7551 is designed to protect voltage sensitive components that require ultra-low capacitance from ESD and transient voltage events. Excellent clamping capability, low capacitance, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its low capacitance, the part is well suited for use in high frequency designs such as USB 2.0 high speed and antenna line applications.

Features

- Ultra-Low Capacitance (0.35 pF Max)
- Low Clamping Voltage
- Stand-off Voltage: 3.3 V
- Low Leakage
- Response Time is < 1 ns
- Low Dynamic Resistance < 1 Ω
- Protection for the Following Standards: IEC 61000-4-2 (Level 4) & ISO 10605
- SZESD7551MXWT5G Wettable Flank Package for Optimal Automated Optical Inspection (AOI)
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- RF Signal ESD Protection
- RF Switching, PA, and Antenna ESD Protection
- Near Field Communications

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Total Power Dissipation on FR–5 Board (Note 1) @ $T_A = 25^{\circ}C$	PD	250	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	400	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	–55 to +150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	ΤL	260	°
IEC 61000-4-2 Contact IEC 61000-4-2 Air ISO 10605 150 pF/2 kΩ ISO 10605 330 pF/2 kΩ ISO 10605 330 pF/330 Ω	ESD	±25 ±25 ±30 ±30 ±20	kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

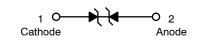
1. $FR-5 = 1.0 \times 0.75 \times 0.62$ in.

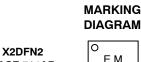
See Application Note AND8308/D for further description of survivability specs.



ON Semiconductor®

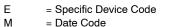
www.onsemi.com







CASE 714AB





FM

F = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping [†]
ESD7551N2T5G	X2DFN2 (Pb-Free)	8000 / Tape & Reel
SZESD7551N2T5G	X2DFN2 (Pb-Free)	8000 / Tape & Reel
SZESD7551MXWT5G	X2DFNW2 (Pb-Free)	8000 / Tape & Reel

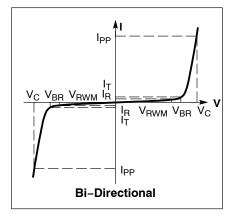
+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

M = Date Code

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

	,
Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ I _{PP}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
Ι _Τ	Test Current



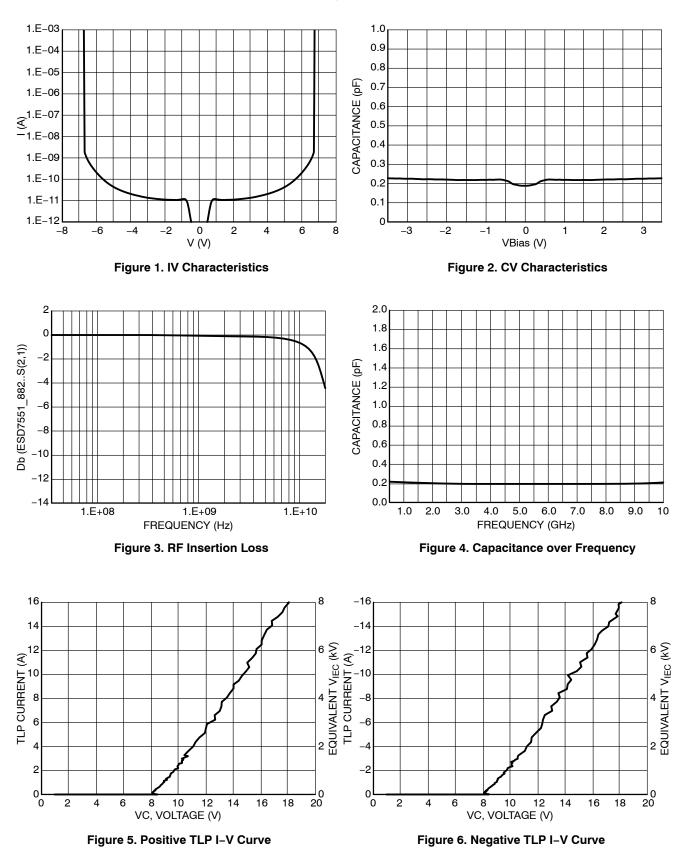
*See Application Note AND8308/D for detailed explanations of datasheet parameters.

ELECTRICAL CHARACTERISTICS (T_A = 25° C unless otherwise specified)

Parameter Symbol		Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V _{RWM}				3.3	V
Breakdown Voltage (Note 2)	V _{BR}	I _T = 1 mA	5.0	6.0	7.5	V
Reverse Leakage Current	I _R	V _{RWM} = 3.3 V		< 1.0	50	nA
Clamping Voltage (Note 3)	V _C	I _{PP} = 1 A			10	V
Clamping Voltage (Note 3)	V _C	I _{PP} = 3 A			13	V
ESD Clamping Voltage	V _C	Per IEC61000-4-2				
Junction Capacitance	CJ				0.35 0.35	pF
Dynamic Resistance	R _{DYN}	TLP Pulse		0.55		Ω

2. Breakdown voltage is tested from pin 1 to 2 and pin 2 to 1. 3. Non-repetitive current pulse at $T_A = 25^{\circ}C$, per IEC61000–4–5 waveform.

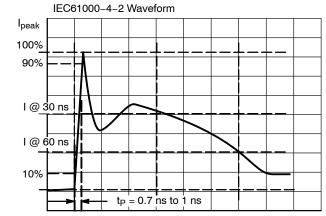
ESD7551, SZESD7551

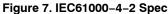


ESD7551, SZESD7551

IEC 61000-4-2 Spec.

Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8





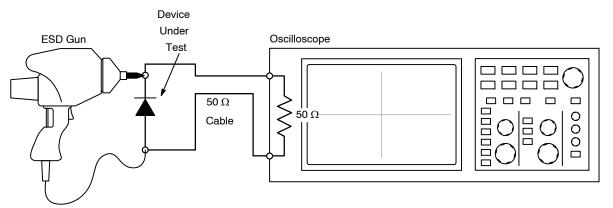
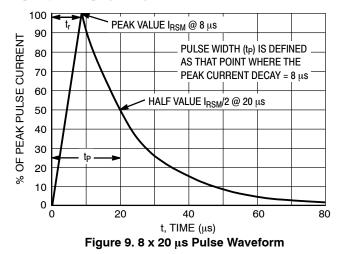


Figure 8. Diagram of ESD Test Setup

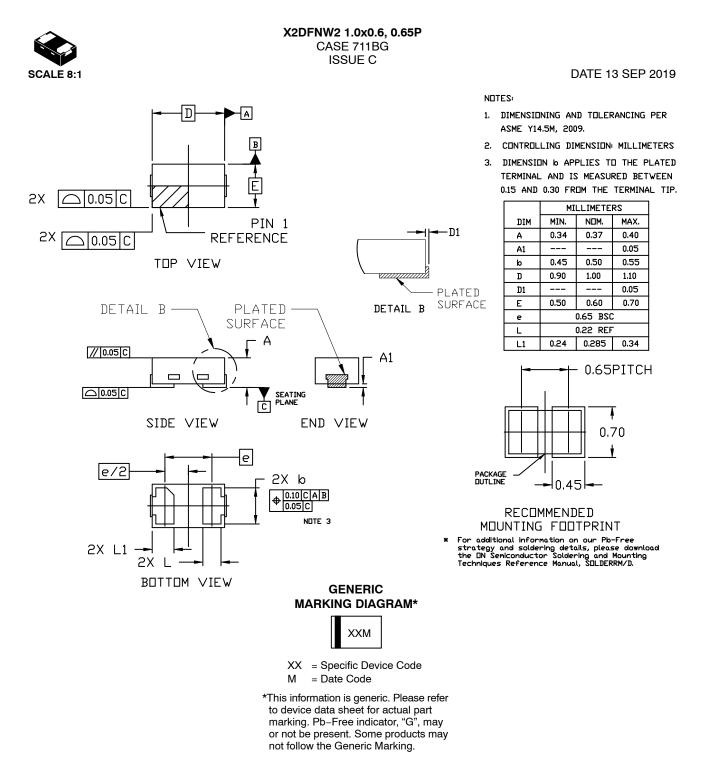
ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000–4–2 waveform. Since the IEC61000–4–2 was written as a pass/fail spec for larger systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage

at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.







DOCUMENT NUMBER:	98AON15241G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	X2DFNW2 1.0X0.6, 0.65P		PAGE 1 OF 1		
ON Semiconductor and ()) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product rights nor the disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the					

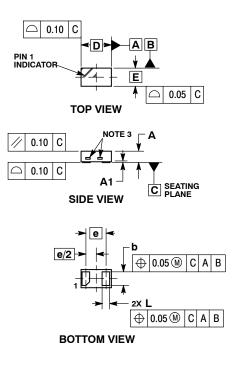
© Semiconductor Components Industries, LLC, 2019

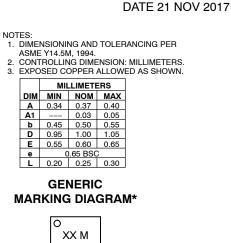
rights of others.





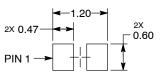
SCALE 8:1





XX = Specific Device Code M = Date Code

RECOMMENDED SOLDER FOOTPRINT*



DIMENSIONS: MILLIMETERS

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON98172F	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	X2DFN2 1.0X0.6, 0.65P		PAGE 1 OF 1		
ON Semiconductor and (1) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the					

X2DFN2 1.0x0.6, 0.65P CASE 714AB ISSUE B

rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent_Marking.pdf</u>. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or indental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification. Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs,

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation onsemi Website: www.onsemi.com

ONLINE SUPPORT: <u>www.onsemi.com/support</u> For additional information, please contact your local Sales Representative at <u>www.onsemi.com/support/sales</u>